

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended) A field effect transistor comprising:
 - a III group nitride semiconductor layer structure including hetero junction;
 - a source electrode and a drain electrode that are so formed on said semiconductor layer structure as to be separated from each other;
 - a gate electrode formed on said semiconductor layer and between said source electrode and said drain electrode; and
 - an insulating film formed on said semiconductor layer structure,
 - wherein said gate electrode has a field plate portion that projects towards said drain electrode in the form of an eave and that is formed on said insulating film; and
 - wherein a thickness of a portion of said insulating film lying between said field plate portion and said semiconductor layer structure gradually increases from said gate electrode toward said drain electrode.
 2. (original) The field effect transistor according to Claim 1, wherein said semiconductor layer structure has an AlGaN/GaN hetero structure.
 3. (previously presented) The field effect transistor according to Claim 1, wherein said thickness of said portion of said insulating film varies stepwise.

4. (currently amended) A field effect transistor-comprising:
 - a III group nitride semiconductor layer structure including hetero junction;
 - a source electrode and a drain electrode that are so formed on said semiconductor layer structure as to be separated from each other;
 - a gate electrode formed on said semiconductor layer and between said source electrode and said drain electrode; and
 - an insulating film formed on said semiconductor layer structure,
 - wherein said gate electrode has a field plate portion that projects towards said drain electrode in the form of an eave and that is formed on said insulating film;
 - wherein a thickness of a portion of said insulating film lying between said field plate portion and said semiconductor layer structure gradually increases from said gate electrode toward said drain electrode, and
 - wherein said thickness of said portion of said insulating film varies continuously.
5. (previously presented) The field effect transistor according to Claim 1, wherein said insulating film is a SiON film.
6. (previously presented) The field effect transistor according to Claim 1, wherein said insulating film is a SiO₂ film or a SiN film.
7. (previously presented) The field effect transistor according to Claim 1, wherein said insulating film is a laminated layer of a SiO₂ film and a SiN film.

8. (previously presented) The field effect transistor according to Claim 1, wherein a drain field plate electrode connected to said drain electrode is arranged on said insulating film between said gate electrode and said drain electrode.
9. (currently amended) The field effect transistor according to Claim 1, wherein the size length of said field plate portion does not exceed 70% of an interval between said gate electrode and said drain electrode.
10. (currently amended) The field effect transistor according to Claim 4, wherein the size length of said field plate portion does not exceed 70% of an interval between said gate electrode and said drain electrode.
11. (previously presented) The field effect transistor according to Claim 1, wherein a thickness of said field plate portion gradually decreases from said gate electrode toward said drain electrode.
12. (currently amended) The field effect transistor according to Claim 1, wherein the entire size-length of said field plate portion that extends to said drain electrode is 0.5 μm or more and preferably 0.7 μm or more.
13. (currently amended) The field effect transistor according to Claim 4, wherein the entire size-length of said field plate portion that extends to said drain electrode is 0.5 μm or more and preferably 0.7 μm or more.

14. (currently amended) The field effect transistor according to Claim 9, wherein the entire size-length of said field plate portion that extends to said drain electrode is 0.5 μm or more and preferably 0.7 μm or more.

15. (currently amended) The field effect transistor according to Claim 10, wherein the entire size-length of said field plate portion that extends to said drain electrode is 0.5 μm or more and preferably 0.7 μm or more.